

rough surface processing, resulting in non-uniform thickness. The chip 12 has such a structure that once it is detached from the board 3 and deforms due to stress, it returns to the level shape only with great difficulties.

The structure thereby never allows the chip 12 to completely return to the level shape even by, for example, vacuum adsorption on a level base. To put it differently, the chip 12, once deformed, by no means completely returns to the level shape. Nor can any analysis be conducted on the LSI 26 and other circuits, once the chip 12 is deformed, as described earlier.

Only a part of the back 12a of the chip 12 needs to be subjected to rough surface processing, to which part is applied stress. The processing may be carried out by means of, for example, scraping by dicing, or sand blast, sandpaper or treatment by laser beam projection.

The chip 12 only needs to, when detached from the board 3, at least partially deform due to stress or preferably is such that the transistor section 21 at least partially deforms convexly or concavely.

Further, there are no particular limitations on the materials of the package 8, board 3, anisotropic conducting glue 5, etc. of embodiments 1 and 2. The package 8 may be provided only when required. To put it